

ASSP VOLTAGE DETECTOR

MB3761

VOLTAGE DETECTOR

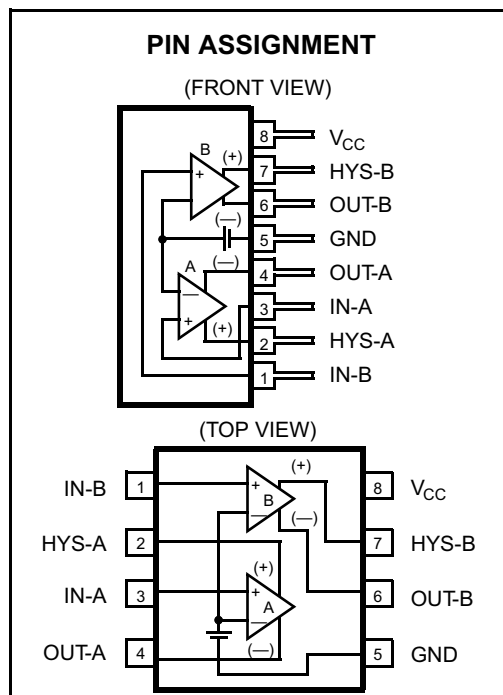
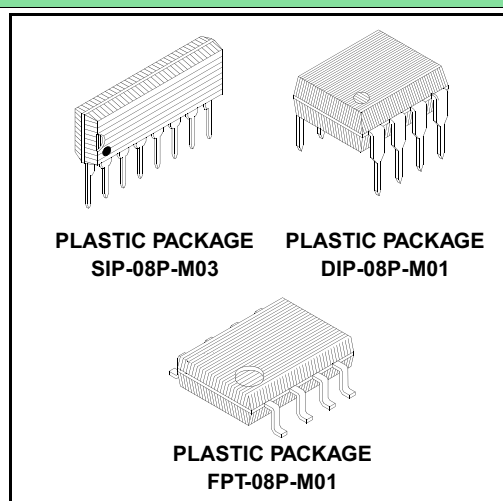
Designed for voltage detector applications, the Fujitsu MB3761 is a dual comparator with a built-in high precision reference voltage generator. Outputs are open-collector outputs and enable use of the OR-connection between both channels. Both channels have hysteresis control outputs. Because of a wide power supply voltage range and a low power supply current, the MB3761 is suitable for power supply monitors and battery backup systems.

- Wide power supply voltage range: 2.5 V to 40 V
- Low power and small voltage dependency supply current: 250 μ A typical.
- Built-in stable low voltage generator: 1.20 V typical.
- Easy-to-add hysteresis characteristics.
- Package: 8-pin Plastic SIP Package (Suffix: -PS)
8-pin Plastic DIP Package (Suffix: -P)
8-pin Plastic FPT Package (Suffix: -PF)

ABSOLUTE MAXIMUM RATINGS (See NOTE)

Rating	Symbol	Value	Unit
Power Supply Voltage	V _{CC}	41	V
Output Voltage	V _O	41	V
Output Current	I _O	50	mA
Input Voltage	V _{IN}	-0.3 to +6.5	V
Power Dissipation	P _D	350 (T _A ≤ 70°C)	mW
Storage Temperature	T _{STG}	-55 to 125	°C

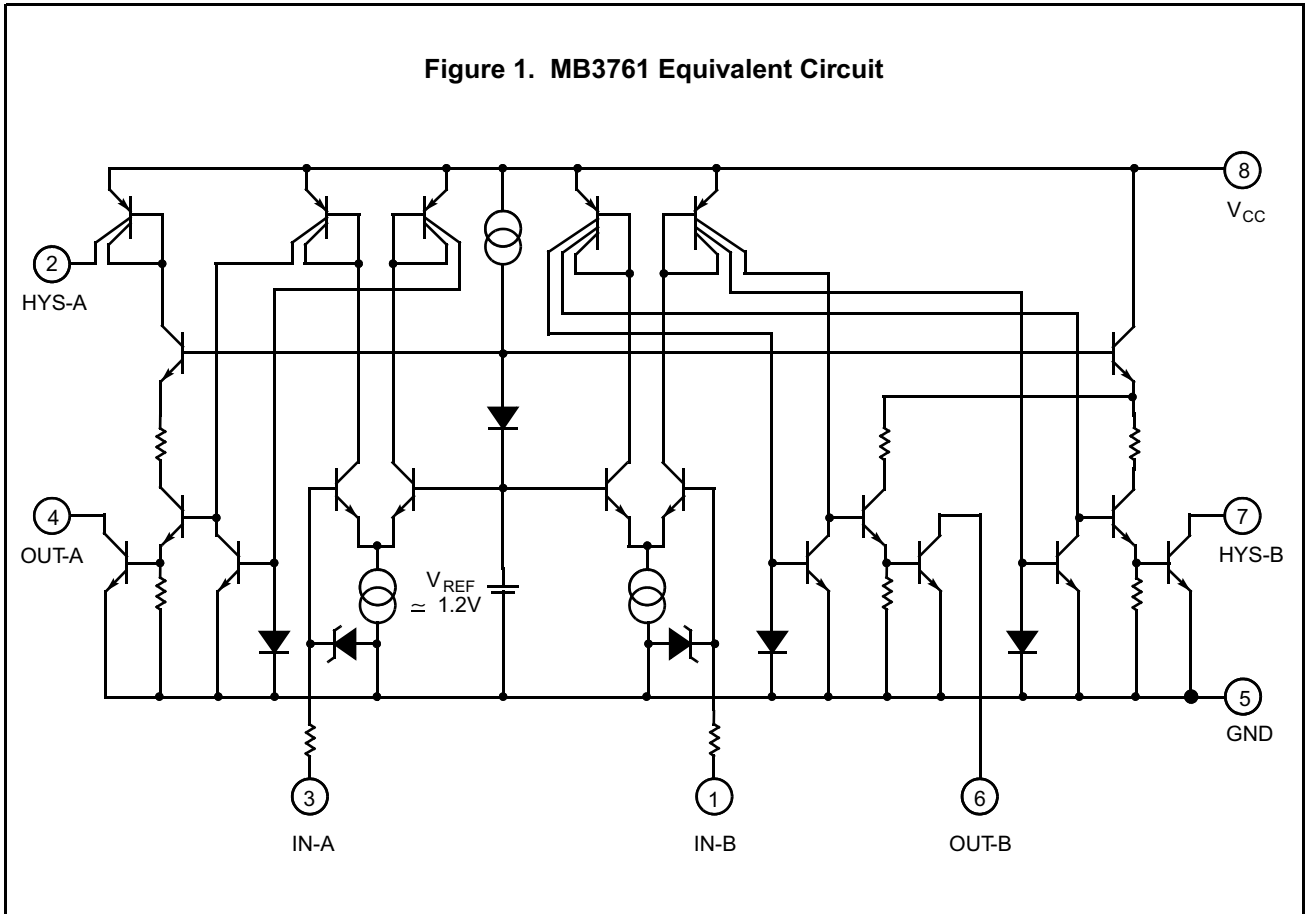
NOTE: Permanent device damage may occur if **ABSOLUTE MAXIMUM RATINGS** are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

MB3761

Figure 1. MB3761 Equivalent Circuit



■ RECOMMENDED OPERATING CONDITIONS

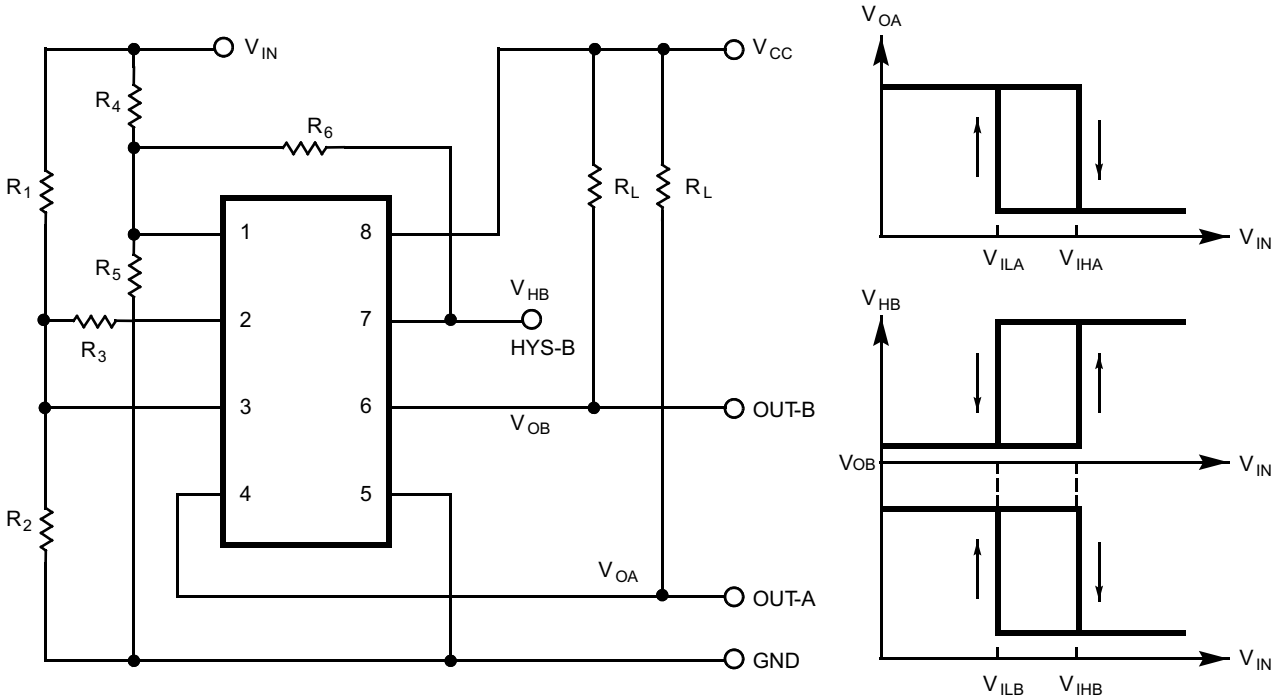
Parameter	Symbol	Value	Unit
Power Supply Voltage	V _{CC}	2.5 to 40	V
Operating Temperature	T _A	-20 to 75	°C
Output Current at pin 4	I _{O4}	4.5	mA
Output Current at pin 6	I _{O6}	3.0	mA

■ ELECTRICAL CHARACTERISTICS

TA=25°C, VCC=5V

Parameter	Designator	Conditions	Values			Unit
			Min	Typ	Max	
Power Supply Voltage	ICCL	VCC=40 V, VIL=1.0 V	-	250	400	μA
	ICCH	VCC=40 V, VIH=1.5 V	-	400	600	μA
Threshold Voltage	VTH	IO =2 mA, VO=1 V	1.15	1.20	1.25	V
Deviation of Threshold Voltage	ΔVTH1	2.5 V ≤ VCC ≤ 5.5 V	-	3	12	mV
	ΔVTH2	4.5 V ≤ VCC ≤ 40 V	-	10	40	mV
Offset Voltage between Outputs	VOOSA	IOA= 4.5 mA, VOA=2 V IHA= 20 mA, VHA=3 V	-	2.0	-	mV
	VOSSB	IOB=3 mA, VOB=2 V IHB=3 mA, VHB=2 V	-	2.0	-	mV
Temperature Coefficient of Threshold Voltage	α	-20°C ≤ TA ≤ 70°C	-	±0.05	-	mV/°C
Difference Voltage on Threshold Voltage between Channel	ΔVTHAB		-10	-	-10	mV
Input Current	IIL	VIL=1.0 V	-	5		nA
	IIH	VIH=1.5 V	-	100	500	nA
Output Leakage Current	IOH	VO=40 V, VIL=1.0 V	-	-	1	μA
Hysteresis Output Leakage Current	IHLA	VCC=40 V, VHA=0 V, VIL=1.0 V	-	-	0.1	μA
	IHHB	VHB=40 V, VIH=1.5 V	-	-	1	μA
Output Sink Current	IOLA	VO=1.0 V, VIH=1.5 V	6	12	-	mA
	IOLB	VO=1.0 V, VIH=1.5 V	4	10	-	mA
Hysteresis Current	IHHA	VH=0 V, VIH=1.5 V	40	80	-	μA
	IHLB	VH=1.0 V, VIL=1.0 V	4	10	-	mA
Output Saturation Voltage	VOLA	IO= 4.5 mA, VIH=1.5 V	-	120	400	mV
	VOLB	IO= 3.0 mA, VIH=1.5 V	-	120	400	mV
Hysteresis Saturation	VHHA	IH= 20 μA, VIH=1.5 V	-	50	200	mV
	VHLB	IH= 3.0 mA, VIL=1.0 V	-	120	400	mV
Output Delay Time	tPHL	RL=5 KΩ	-	2	-	μs
	tPLH	RL=5 KΩ	-	3	-	μs

Figure 2. Operational Definitions



$$V_{IHA} = (1 + \frac{R_1}{R_2}) V_R$$

$$V_{IHB} = (1 + \frac{R_4}{R_5 // R_6}) V_R$$

NOTE)

$$V_R \approx V_{TH} (\approx 1.20V)$$

$$V_{ILA} = (1 + \frac{R_1}{R_2 // R_3}) V_R - \frac{R_1}{R_3} V_{CC}$$

$$V_{ILB} = (1 + \frac{R_4}{R_5}) V_R$$

$$R_2 // R_3 = \frac{R_2 R_3}{R_2 + R_3}$$

$$R_5 // R_6 = \frac{R_5 R_6}{R_5 + R_6}$$

■ TYPICAL PERFORMANCE CHARACTERISTICS

Fig. 3 - Power Supply Current vs Power Supply Voltage

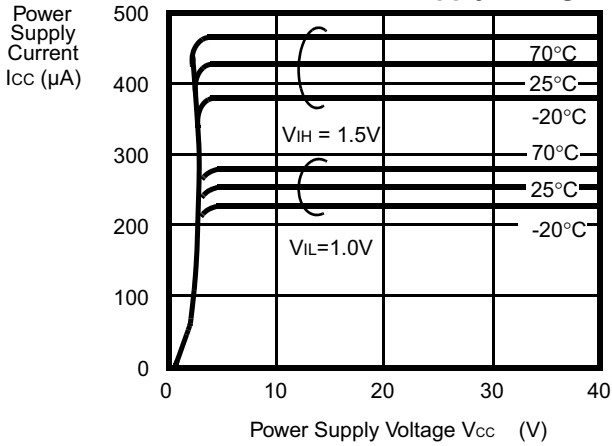


Fig. 4 - Hysteresis (A) Current vs Power Supply Voltage

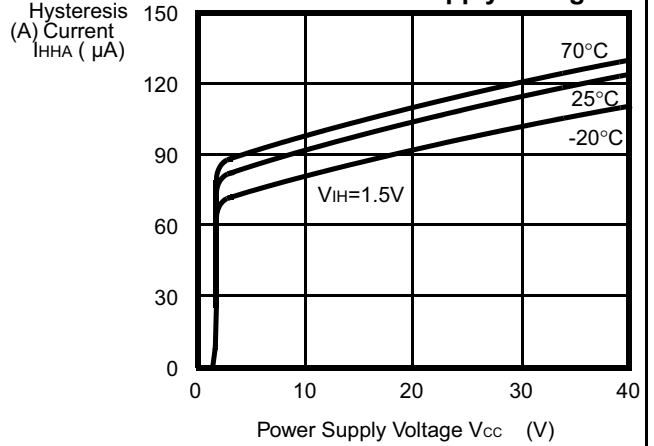


Fig. 5 - Output (A) Voltage vs. Output (A) Current

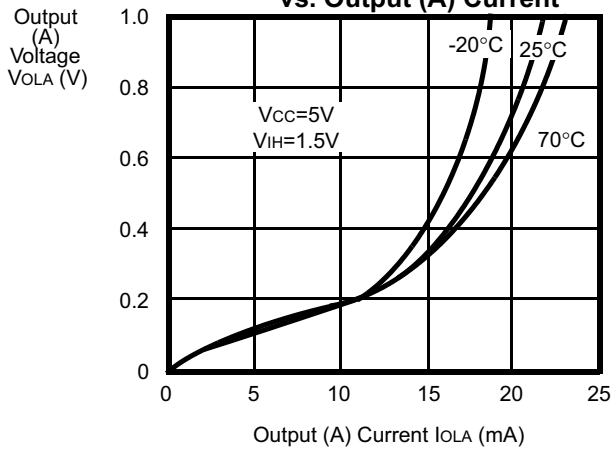


Fig. 6 - Output (B) Voltage vs. Output (B) Current

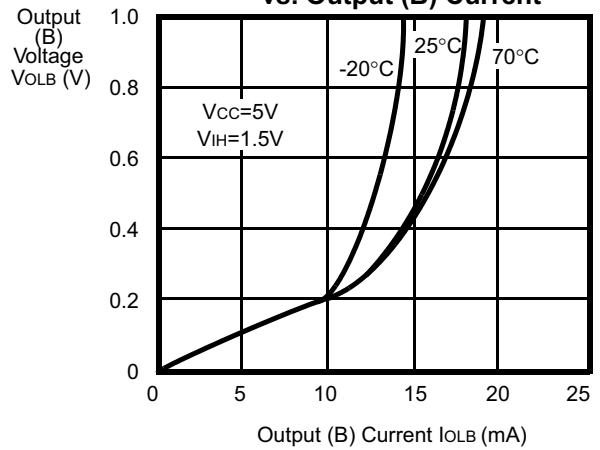


Fig. 7 - Threshold Voltage vs. Power Supply Voltage

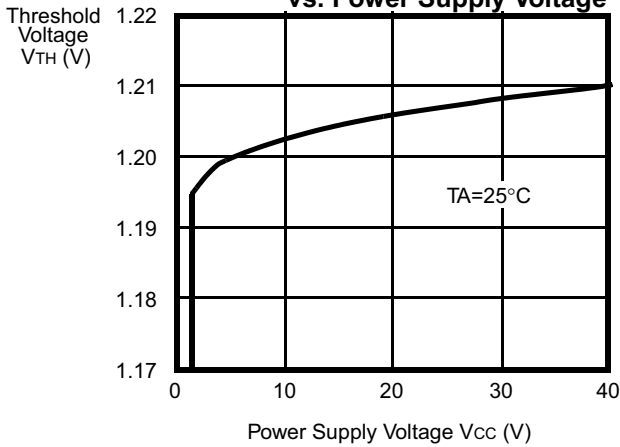
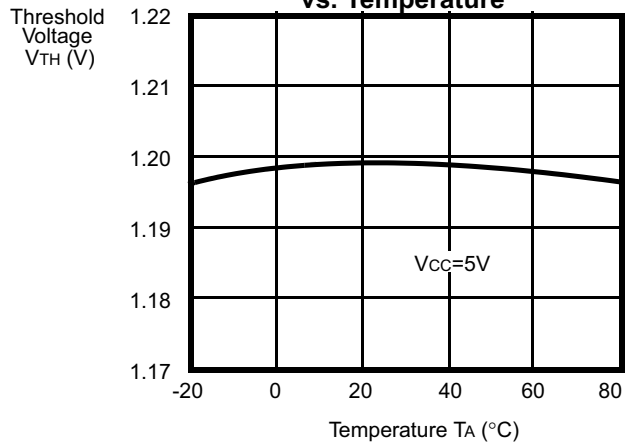
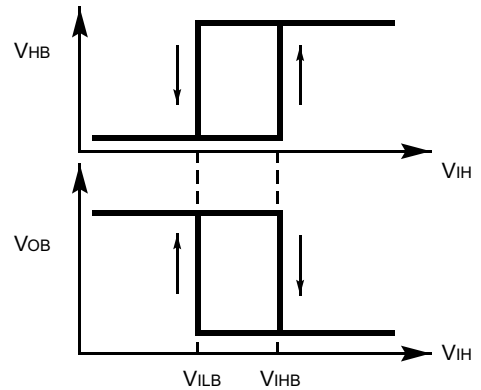
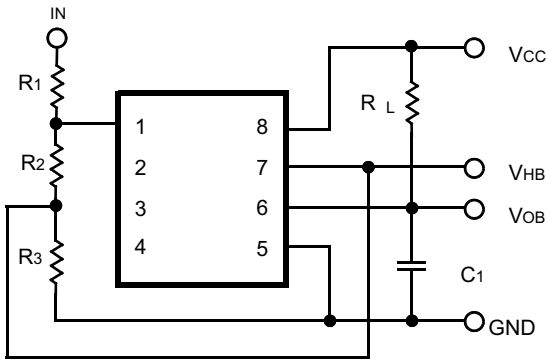
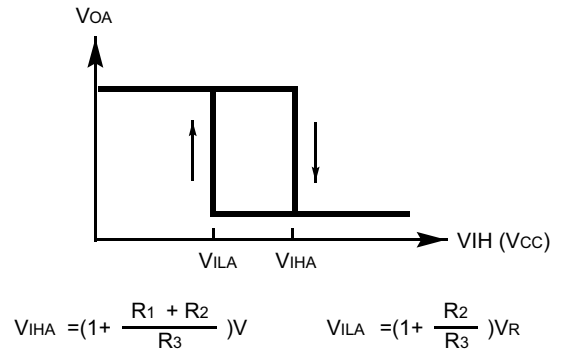
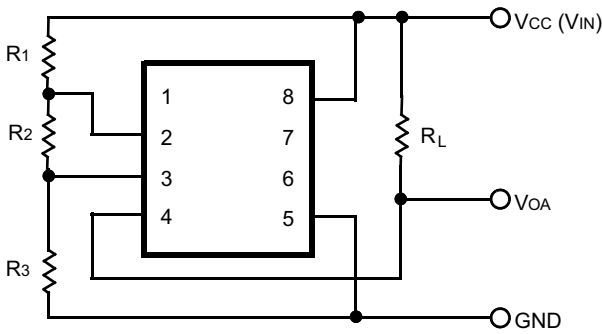


Fig. 8 - Threshold Voltage vs. Temperature



■ APPLICATION EXAMPLES

Figure 9. Addition of Hysteresis



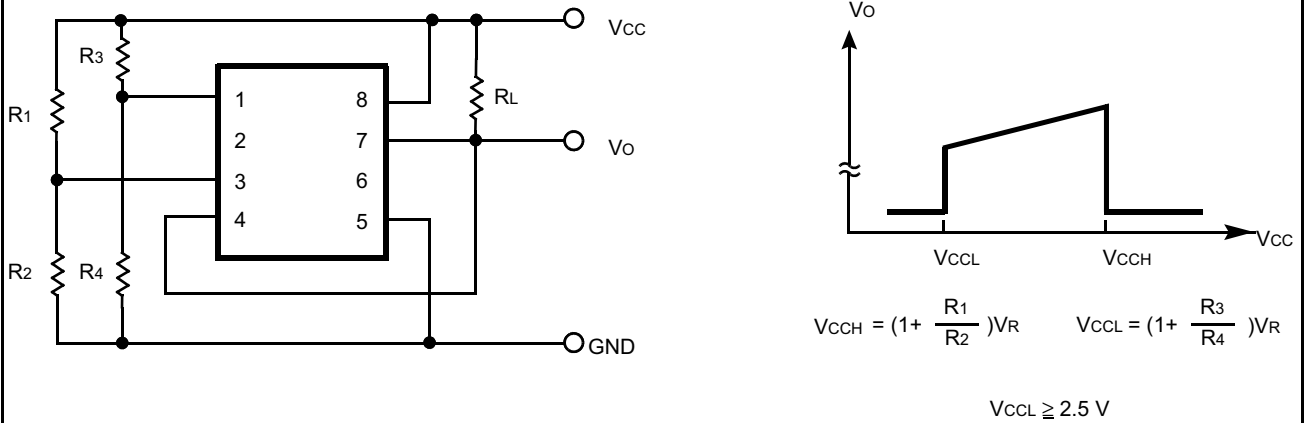
Note: All calculations occur with the output voltage at 0. The hysteresis values are adjusted for load condition and saturation voltage.

$$V_{IHB} = \left(1 + \frac{R_1}{R_2}\right)V_R$$

$$V_{ILB} = \left(1 + \frac{R_1}{R_2 + R_3}\right)V_R$$

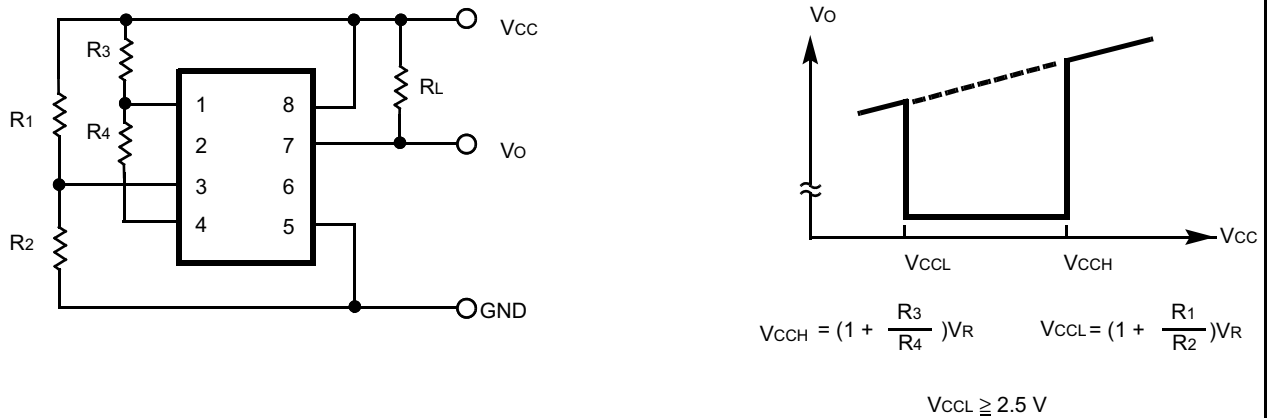
■ APPLICATION EXAMPLES (Continued)

Figure 10. Voltage Detection for Alarm



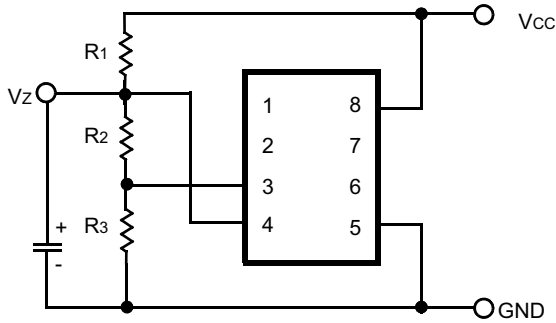
For hysteresis, a positive feedback from pin 2 or 7 is required.

Figure 11. Voltage Detection for Alarm



■ APPLICATION EXAMPLES (Continued)

Figure 12. Programmable Zener

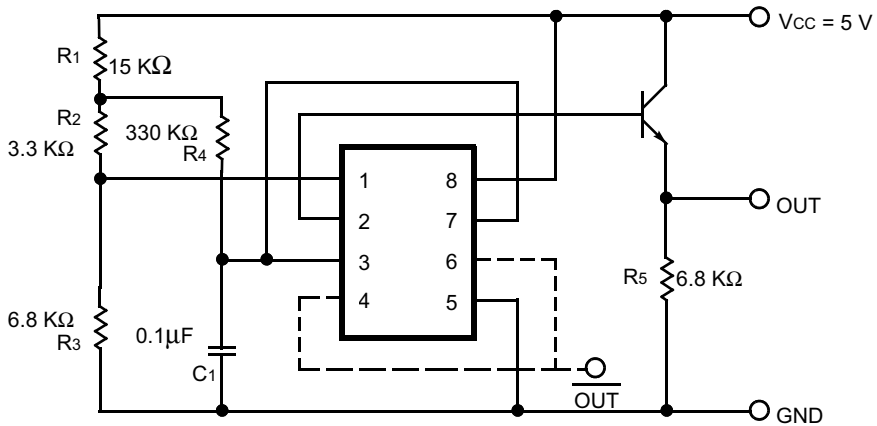


$$V_Z \approx \left(1 + \frac{R_2}{R_3}\right) V_R$$

$$\frac{V_Z}{R_2 + R_3} \leq \frac{V_{CC} - V_Z}{R_1} \leq 6\text{mA}$$

Channel B can be used independently.

Figure 13. Recovery Reset Circuit



■ TYPICAL CHARACTERISTICS

Figure 14. DC Characteristics

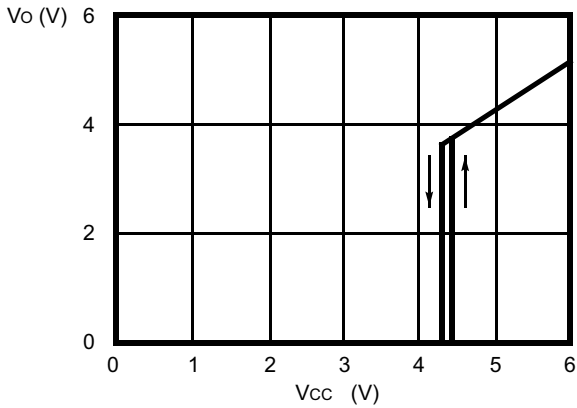
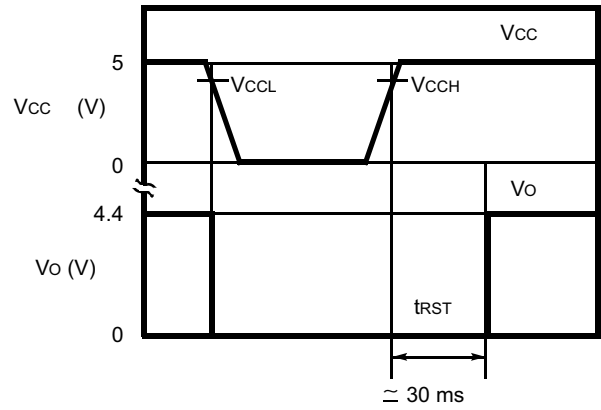


Figure 15. Response Characteristics



- Voltage Threshold Levels (V_{CCL} and V_{CCH}) and Hysteresis Width can be changed by the resistors (R_1 through R_4).

$$V_{CCL} = \frac{R_1 + R_2 + R_3}{R_3} V_{TH}$$

$$V_{CCH} = V_{CCL} + \frac{R_1 (R_2 + R_3)}{R_3 R_4} V_{TH}$$

- Power-On Reset Time is provided by the following approximate equation:

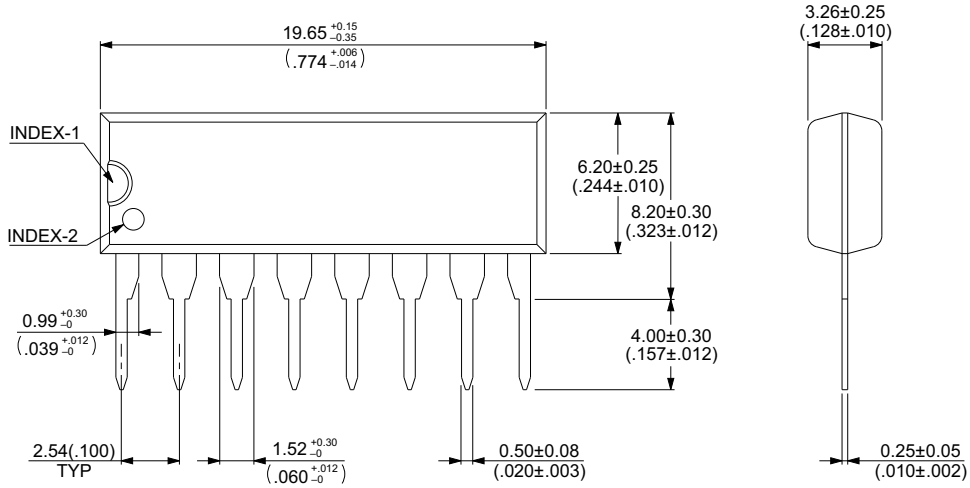
$$t_{RST} = -C_1 R_4 \cdot \ln \left\{ 1 - \frac{V_{TH}}{V_{CC}} \left(1 + \frac{R_1}{R_2 + R_3} \right) \right\}$$

- The recommended value of h_{FE} of the external transistor is from 50 to 200.
- In the case of an instant power fail, the remaining charge in C_1 effects t_{RST} .
- If necessary, the reversed output is provided on HYS terminal

MB3761

■ PACKAGE DIMENSIONS (Continued)

8 pin, Plastic SIP
(SIP-08P-M03)

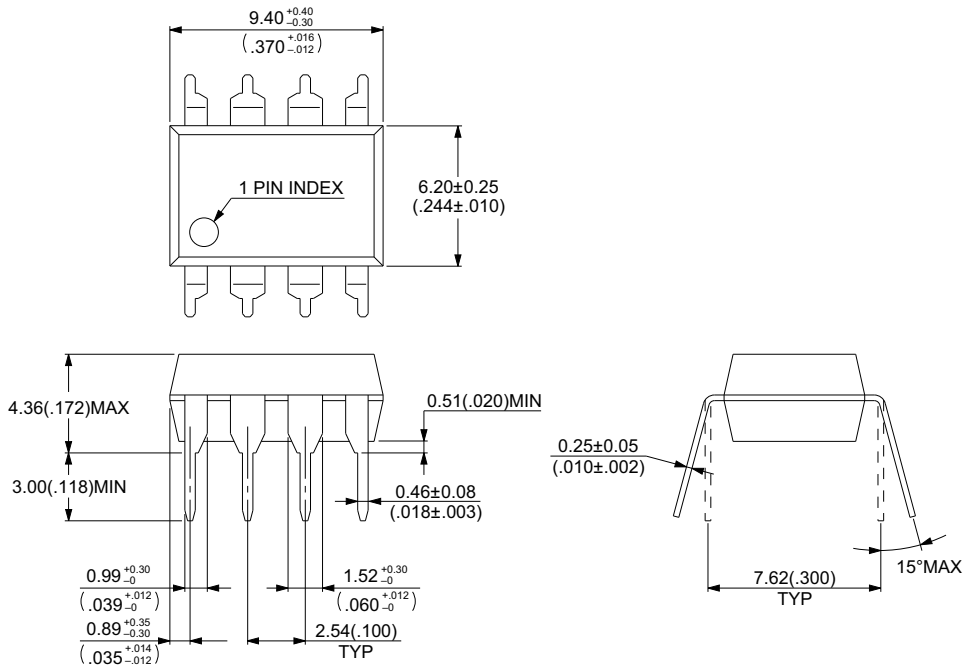


© 1994 FUJITSU LIMITED S08010S-3C-2

Dimensions in mm (inches).

■ PACKAGE DIMENSIONS (Continued)

8 pin, Plastic DIP
(DIP-08P-M01)



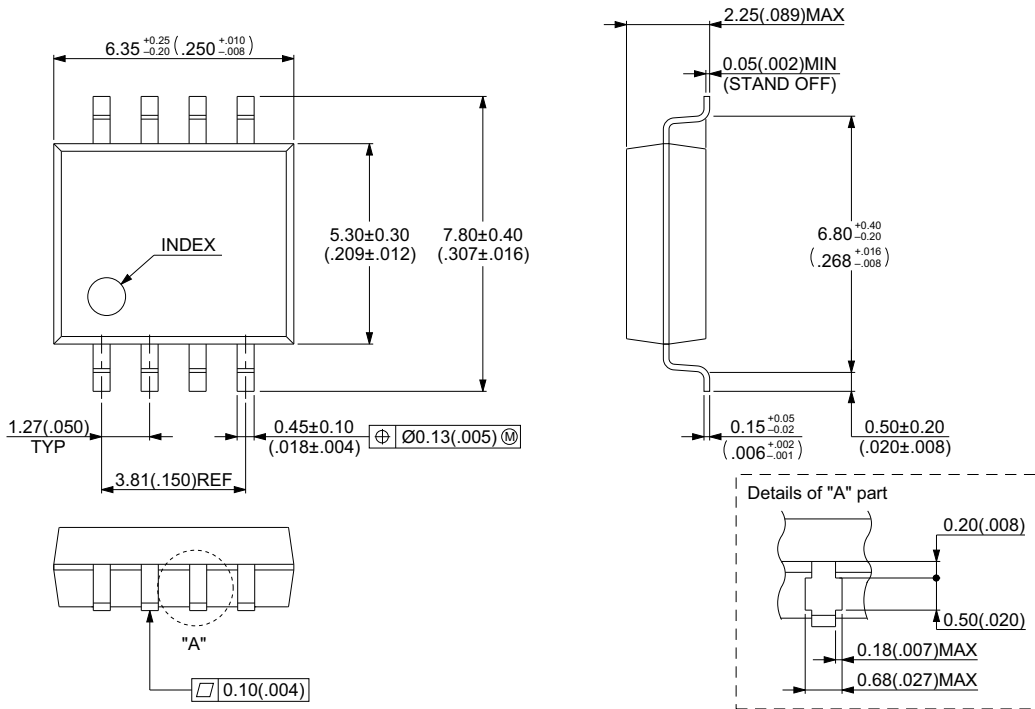
© 1994 FUJITSU LIMITED D08006S-2C-3

Dimensions in mm (inches).

MB3761

■ PACKAGE DIMENSIONS (Continued)

8 pin, Plastic SOP
(FPT-08P-M01)



© 1994 FUJITSU LIMITED F08002S-4C-4

Dimensions in mm(inches).

FUJITSU LIMITED

For further information please contact:

Japan

FUJITSU LIMITED
Corporate Global Business Support Division
Electronic Devices
KAWASAKI PLANT, 4-1-1, Kamikodanaka
Nakahara-ku, Kawasaki-shi
Kanagawa 211-88, Japan
Tel: (044) 754-3763
Fax: (044) 754-3329

North and South America

FUJITSU MICROELECTRONICS, INC.
Semiconductor Division
3545 North First Street
San Jose, CA 95134-1804, U.S.A.
Tel: (408) 922-9000
Fax: (408) 432-9044/9045

Europe

FUJITSU MIKROELEKTRONIK GmbH
Am Siebenstein 6-10
63303 Dreieich-Buchsschlag
Germany
Tel: (06103) 690-0
Fax: (06103) 690-122

Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE. LIMITED
#05-08, 151 Lorong Chuan
New Tech Park
Singapore 556741
Tel: (65) 281-0770
Fax: (65) 281-0220

All Rights Reserved.

The contents of this document are subject to change without notice. Customers are advised to consult with FUJITSU sales representatives before ordering.

The information and circuit diagrams in this document presented as examples of semiconductor device applications, and are not intended to be incorporated in devices for actual use. Also, FUJITSU is unable to assume responsibility for infringement of any patent rights or other rights of third parties arising from the use of this information or circuit diagrams.

FUJITSU semiconductor devices are intended for use in standard applications (computers, office automation and other office equipment, industrial, communications, and measurement equipment, personal or household devices, etc.).

CAUTION:

Customers considering the use of our products in special applications where failure or abnormal operation may directly affect human lives or cause physical injury or property damage, or where extremely high levels of reliability are demanded (such as aerospace systems, atomic energy controls, sea floor repeaters, vehicle operating controls, medical devices for life support, etc.) are requested to consult with FUJITSU sales representatives before such use. The company will not be responsible for damages arising from such use without prior approval.

Any semiconductor devices have inherently a certain rate of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions.

If any products described in this document represent goods or technologies subject to certain restrictions on export under the Foreign Exchange and Foreign Trade Control Law of Japan, the prior authorization by Japanese government should be required for export of those products from Japan.

F9703

© FUJITSU LIMITED Printed in Japan